



STripFET™ N - CHANNEL 30V - 0.018Ω - 8A S0-8
MOSFET PLUS SCHOTTKY RECTIFIER



SO-8

INTERNAL SCHEMATIC DIAGRAM

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage ($V_{GS} = 0$)	30	V
V_{DGR}	Drain- gate Voltage ($R_{GS} = 20\text{ k}\Omega$)	30	V
V_{GS}	Gate-source Voltage	± 20	V
I_D	Drain Current (continuous) at $T_c = 25\text{ }^\circ\text{C}$	8	A
I_D	Drain Current (continuous) at $T_c = 100\text{ }^\circ\text{C}$	5	A
$I_{DM}(\bullet)$	Drain Current (pulsed)	32	A
P_{tot}	Total Dissipation at $T_c = 25\text{ }^\circ\text{C}$	2.5	W

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		30	V
$I_{F(RMS)}$	RMS Forward Current		20	A
$I_{F(AV)}$	Average Forward Current	$T_L=125\text{ }^{\circ}\text{C}$ $\delta =0.5$	3	A
I_{FSM}	Surge Non Repetitive Forward Current	tp= 10 ms Sinusoidal	75	A
I_{RSM}	Non Repetitive Peak Reverse Current	tp=100 μ s	1	A
dv/dt	Critical Rate Of Rise Of Reverse Voltage		10000	V/ μ s

(●) Pulse width limited by safe operating area

THERMAL DATA

R _{thj-amb}	(*) Thermal Resistance Junction-ambient MOSFET	50	°C/W
R _{thj-amb}	(*) Thermal Resistance Junction-ambient SCHOTTKY	100	°C/W
T _{stg}	Storage Temperature Range	-65 to 150	°C
T _j	Junction Temperature	150	°C
(*) mounted on FR-4 board (steady state)			

MOSFET ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	1	1.6	2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 4 A V _{GS} = 4.5V I _D = 4 A		0.018 0.021	0.022 0.026	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	8			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 4 A		10		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		1050 250 85		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 15\text{ V}$ $I_D = 4\text{ A}$		22		ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, see fig. 3)		60		ns
Q_g	Total Gate Charge	$V_{DD} = 24\text{ V}$ $I_D = 8\text{ A}$ $V_{GS} = 4.5\text{ V}$		17.5	23	nC
Q_{gs}	Gate-Source Charge			4		nC
Q_{gd}	Gate-Drain Charge			7		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 15\text{ V}$ $I_D = 4\text{ A}$		42		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, see fig. 3)		10		ns
$t_{r(voff)}$	Off-voltage Rise Time	$V_{DD} = 24\text{ V}$ $I_D = 8\text{ A}$		11		ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$		12		ns
t_c	Cross-over Time	(Inductive Load, see fig. 5)		25		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				8	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				32	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 8\text{ A}$ $V_{GS} = 0$			2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 8\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		50		ns
Q_{rr}	Reverse Recovery Charge			40		nC
I_{RRM}	Reverse Recovery Current			1.6		A

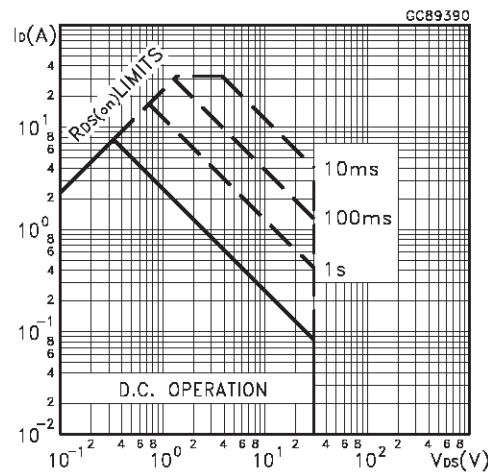
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

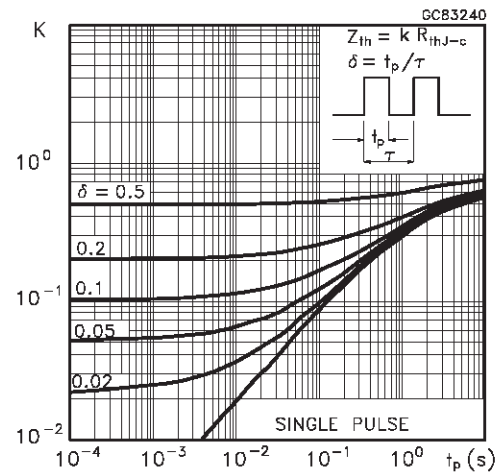
SCHOTTKY STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_R(*)$	Reversed Leakage Current	$T_J = 25\text{ }^\circ\text{C}$ $V_R = 30\text{ V}$ $T_J = 125\text{ }^\circ\text{C}$ $V_R = 30\text{ V}$		0.03	0.2 100	mA mA
$V_F(*)$	Forward Voltage drop	$T_J = 25\text{ }^\circ\text{C}$ $I_F = 3\text{ A}$ $T_J = 125\text{ }^\circ\text{C}$ $I_F = 3\text{ A}$		0.38	0.51 0.46	V V

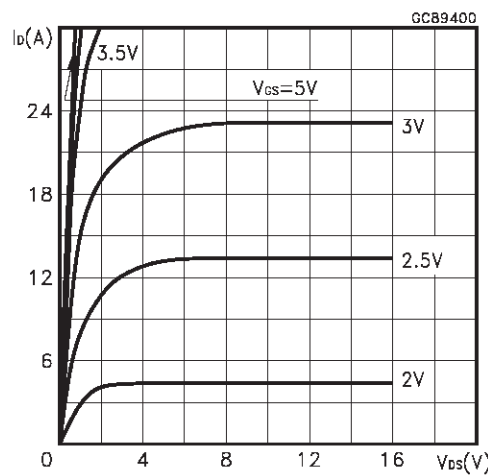
Safe Operating Area



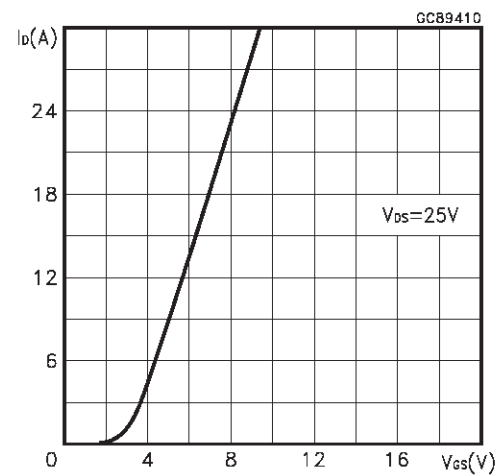
Thermal Impedance



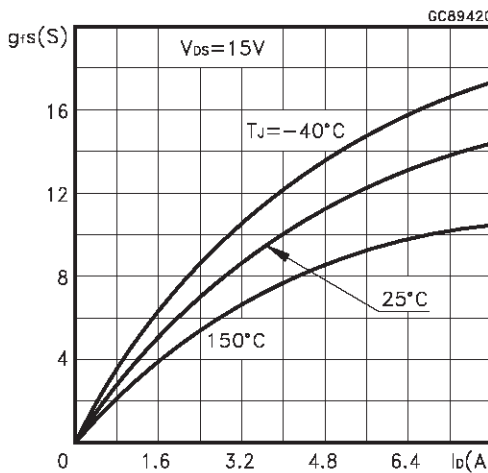
Output Characteristics



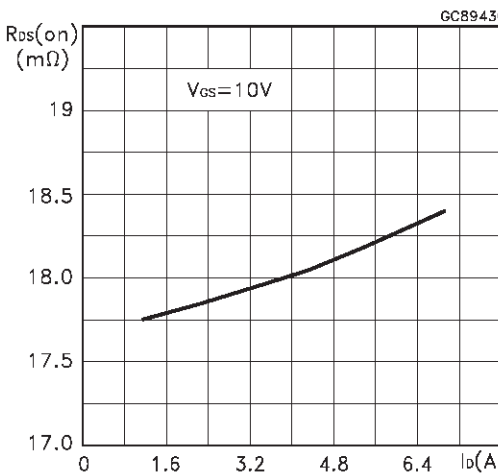
Transfer Characteristics



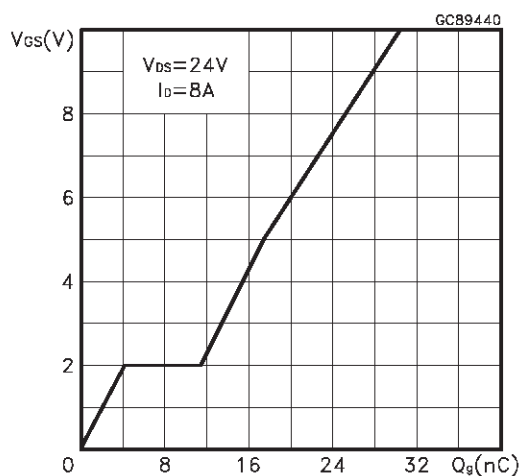
Transconductance



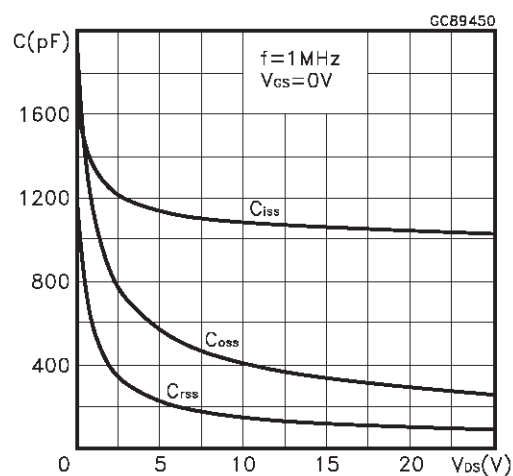
Static Drain-source On Resistance



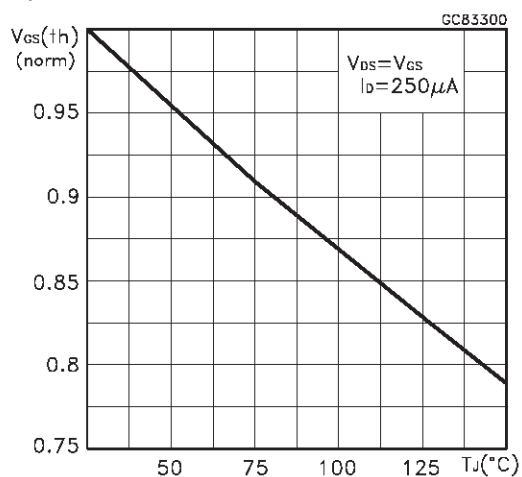
Gate Charge vs Gate-source Voltage



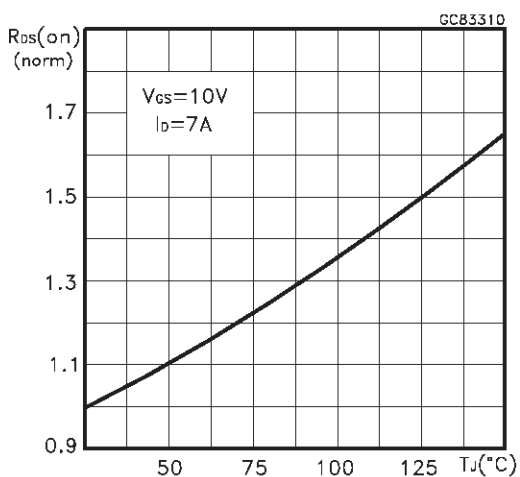
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

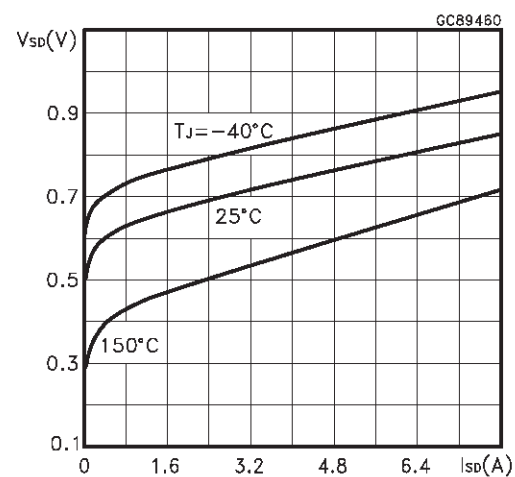


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform



Fig. 3: Switching Times Test Circuits For Resistive Load



Fig. 4: Gate Charge test Circuit

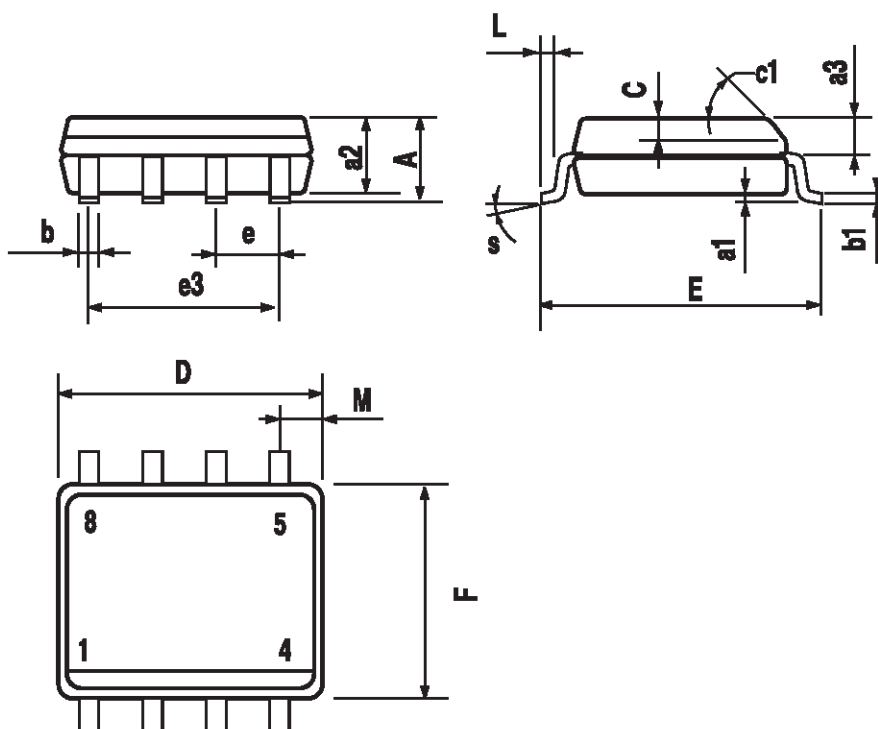


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



SO-8 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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